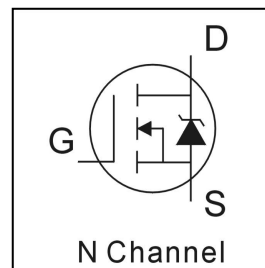


## N Channel Power MOSFET

## Chip Specification

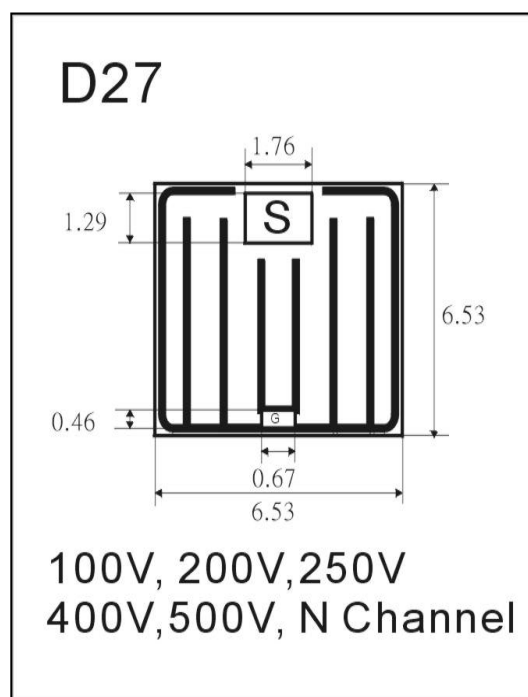
## General Description:

- \* Advanced Process Technology
- \* Dynamic dV/dt Rating
- \* **150°C Operating Temperature**
- \* **Fast Switching**
- \* **Fully Avalanche Rated**



## Mechanical Data:

| D27                           |                                |
|-------------------------------|--------------------------------|
| Dimension                     | 6.53mm x 6.53mm                |
| Thickness:                    | 400 μm                         |
| Metallization:                |                                |
| Top :                         | Al                             |
| Backside :                    | CrNiAg / Au                    |
| Suggested Bonding Conditions: |                                |
| Die Mounting:                 | Solder Perform                 |
|                               | 95/5 PbSn or 92.5/2.5/5 PbAgIn |
| Source Bonding Wire:          | 20 mil Al                      |



## Absolute Maximum Rating

@Ta=25°C

| Characteristics                               | Symbol   | Limit   | Unit | Test Conditions  |
|-----------------------------------------------|----------|---------|------|------------------|
| Drain-to-Source Breakdown Voltage             | V(BR)DSS | 250     | V    | VGS=0V, ID=250μA |
| Static Drain-to - Source On-resistance        | RDS(ON)  | 0.14    | Ω    | VGS=10V, ID= 14A |
| Continuous Drain current ( in target package) | ID@25°C  | 23      | A    | VGS=10V          |
| Continuous Drain current ( in target package) | ID@100°C | 15      | A    | VGS=10V          |
| Operation Junction                            | Tj       | -55~150 | °C   |                  |
| Storage Temperature                           | TSTR     | -55~150 | °C   |                  |

## Target Device: IRFP254

TO-247AC

Pd

190

W

@Tc=25°C